## **EAST Search History**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5028	345/92,87.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/09/20 13:37
L2	2324	(TFT(((thin adj film) (field adj effect)) adj transistor) FET) same ((source drain gate) near electrode) same ((positive negative) near (voltage pulse bias))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/09/20 16:52
L3	61	1 and 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/09/20 13:45
L4	52	(TFT(thin adj film adj transistor)) same (FET (field adj effect adj transistor)) same ((source drain gate) near5 (positive negative) near5 (voltage pulse bias))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/09/20 16:58

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